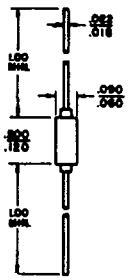
Silicon Switching Diodes
DO-35 Package

DO35 PACKAGE



ABSOLUTE MAXIMUM RATINGS @25°C

Storage Temperature	-65°C to +175°C
Operating Temperature	-65°C to +150°C
Power Dissipation	500 mW

CHARACTERISTICS @ 25°C (UNLESS OTHERWISE NOTED)

TYPE	DO7 EQUIVALENT	BV MIN	@ I(μA)	I_F (mA) AT 1.0V	MAXIMUM REVERSE CURRENT I_R(μA) 25°C	150°C (mA)	@V_R(V)	MAX. CAP. AT V=0 (pf)	T_{RR} (nsec)	AVE. RECTIFIED FORWARD CURRENT (mA)
1N4148	1N914	75(X)	5	10	.025	.05	20	4	4(1)	75
1N4149	1N916	75(X)	5	10	.025	.05	20	2	4(1)	75
1N4150	1N3600	50	100	200(1)	0.1	0.1	50	2.5	10(2)	150
1N4151	1N3604	75	5	50	.05	.05	50	2	2(1)	150
1N4152	1N3605	40	5	50	.05	.05	30	2	2(1)	150
1N4153	1N3606	75	5	50	.05	.05	50	2	2(1)	150
1N4154	1N4009	35	5	30	0.1	0.1	25	4	2(1)	25
1N4305	1N4063	75	5	50	0.1	0.1	50	2	2(1)	150
1N4444	–	70	5	100	.05	.05	50	2	–	200
1N4446	1N914A	75(X)	5	20	.025	.05	20	4	4(1)	150
1N4447	1N916A	75(X)	5	20	.025	.05	20	2	4(1)	150
1N4448	1N914B	75(X)	5	100	.025	.05	20	4	4(1)	150
1N4449	1N916B	75(X)	5	30	.025	.05	20	2	4(1)	150
1N4450	–	40(X)	5	200	.05	.05	30	4	4(1)	200
1N4451	–	40	5	300	.05	.05	30	6	–	200
1N4452	–	40	5	600	.05	.05	30	30	50(1)	200
1N4453	–	30	5	100	.05	.05	20	30	–	100
1N4454	1N3064	75	5	10	0.1	.01	50	2	2(1)	75

X – Also Tested At 100V @ 100uA

T_{RR} TEST CONDITIONS

(1) I_F= 10mA Recover to 1mA V_R = 6V R_L = 100 OHMS

(2) $I_F = I_R$ = 10 to 200mA i_{rr} = 0.1

General Purpose Varactor Tuning Diodes

ELECTRICAL CHARACTERISTICS @ Ta=25°C

DEVICE TYPE	CAPACITANCE @ -4Vdc	TYPICAL CAPACITANCE RANGE 0.1Vdc to MWV	QUALITY FACTOR Q @ -4Vdc f=50Mc MIN.	TYP.	REVERSE VOLTAGE @100 uA	MAXIMUM WORKING VOLTAGE
1N950	35	6-88	7	39	150	130
1N951	50	12-120	7	36	100	80
1N952	70	20-270	7	30	75	60
1N953	100	46-240	7	23	30	25
1N954	35	14-88	7	20	30	25
1N955	50	22-120	7	20	30	25
1N956	70	33-120	7	20	30	25

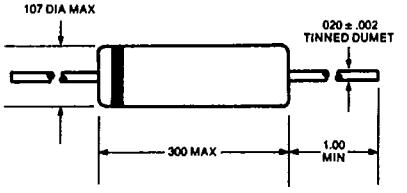
Capacitance Tolerance:

Standard Device.....±20%

Suffix A.....±10%

Suffix B.....±5%

Suffix C.....±2%

Suffix D.....±1%

DO-7 PACKAGE